

Key components technology update of 100W EUV light source for HVM

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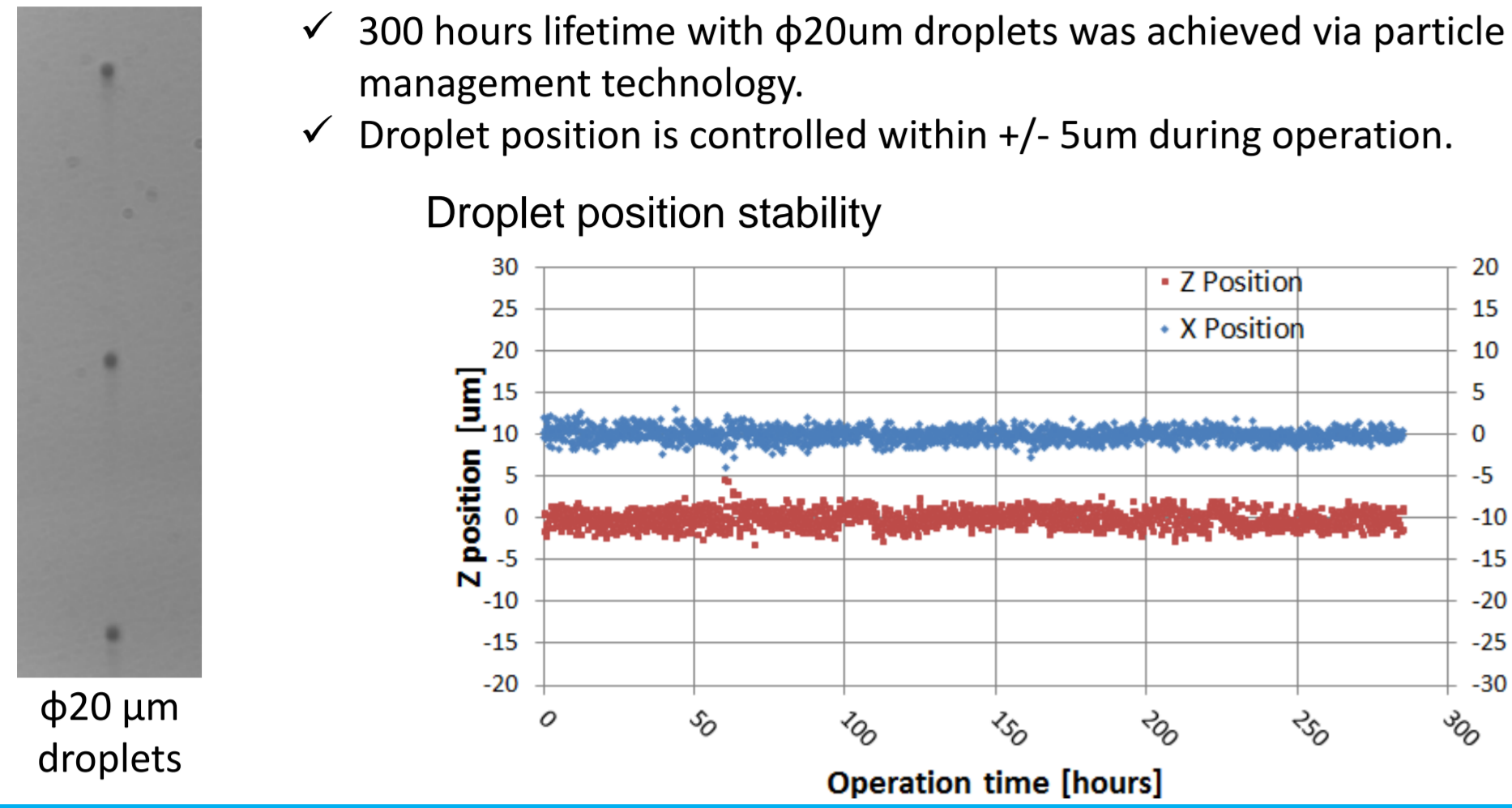


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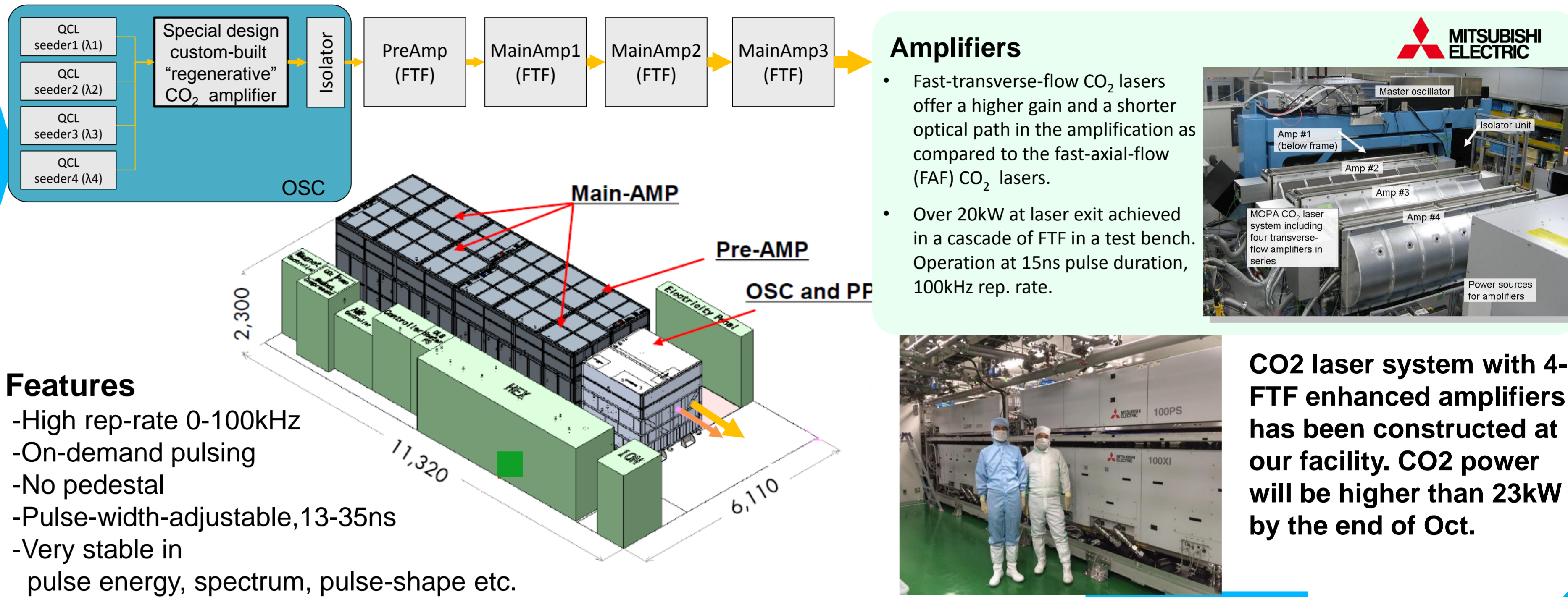
This paper presents a technology update of key components of a 100W LPP-EUV (laser produced plasma extreme ultraviolet) light source for high volume manufacturing which enables sub-10nm critical layer patterning for semiconductor device fabrication. Key components of this EUV light source system from Gigaphoton include a magnetic debris mitigation system, a high power short pulse CO₂ drive laser system, a unique pre-pulse laser system, a small droplets generator and a laser-droplet shooting control system. All components are perfectly controlled and interact harmoniously to produce a stable plasma and to effectively evacuate the Tin debris from the EUV vessel in order to realize a high power and long lifetime EUV light source system. This paper describes the latest results obtained from our proto systems that are based on key components which support a 100 watt LPP-EUV light source.

ABSTRACT

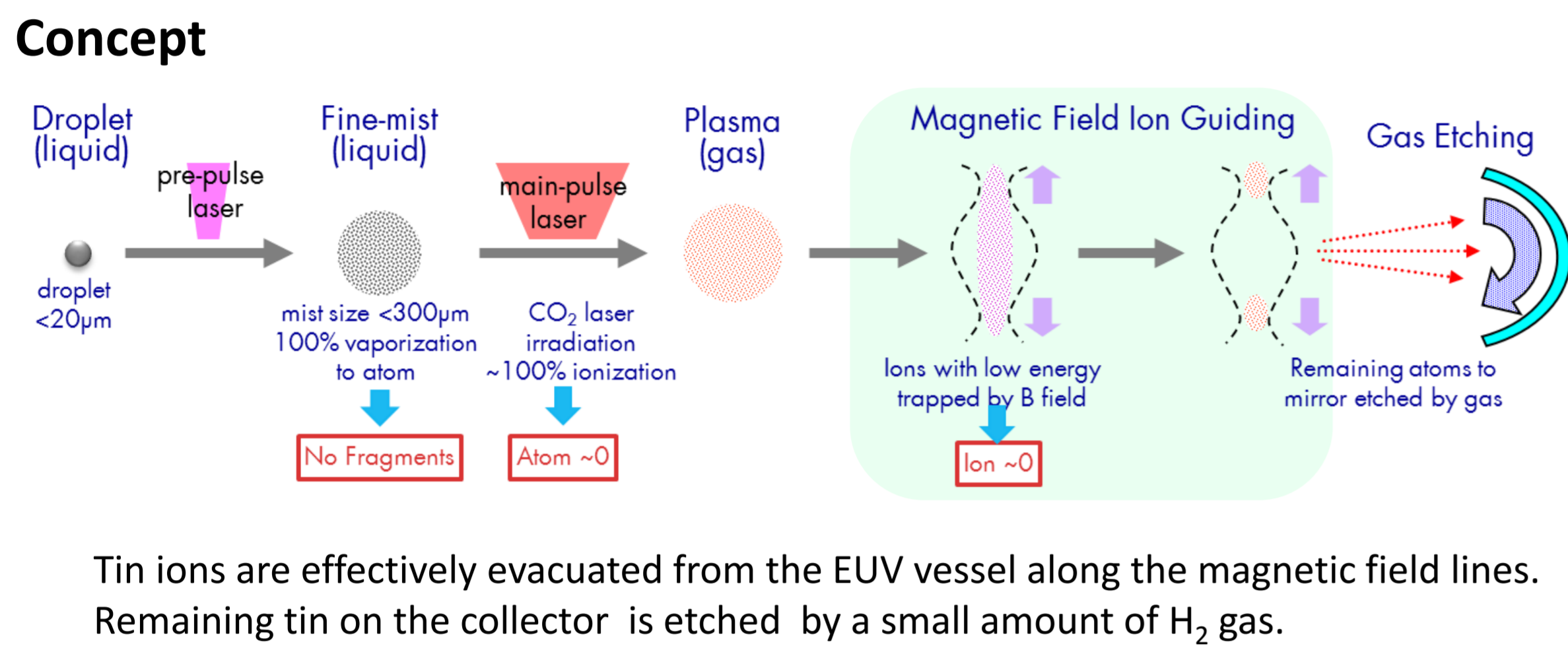
1. Droplet generation and Control



2. Hybrid CO₂ Laser System with short pulse high rep. rate Oscillator and FTF Amplifiers



6. Tin debris mitigation with a superconductive magnet

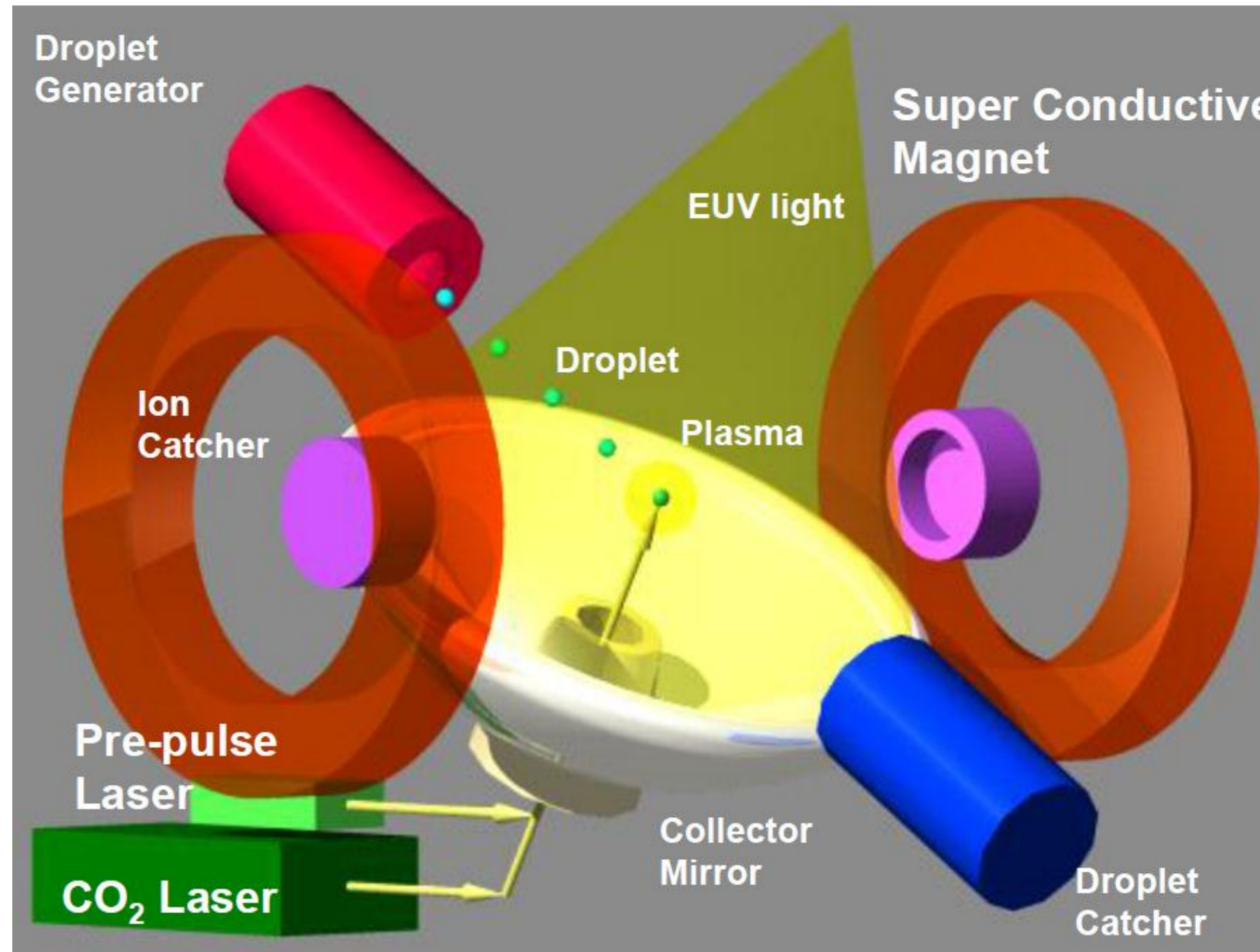


Recent result

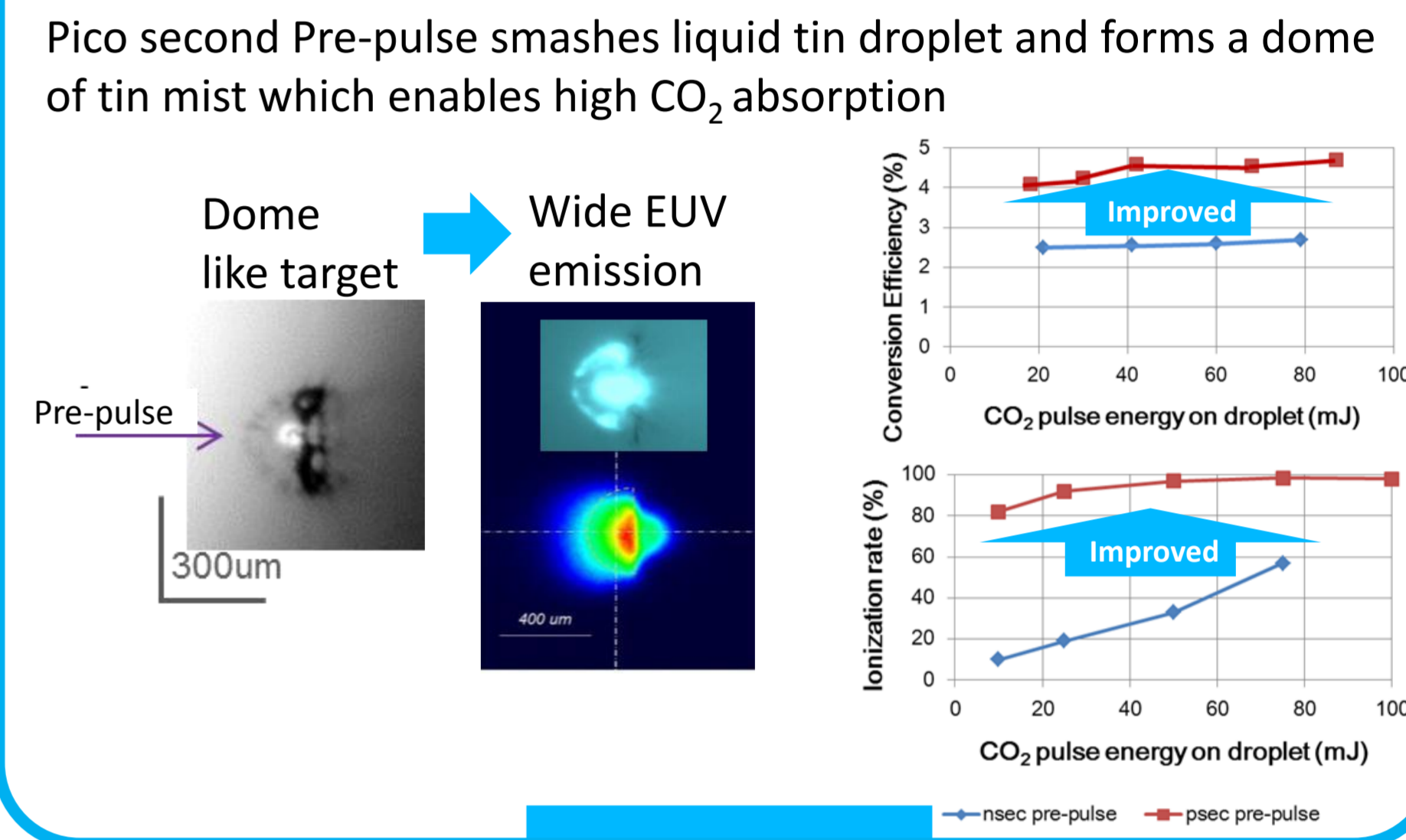
Pulse number	152 Mpls	527 Mpls	1513 Mpls	4531 Mpls
Debris in Center of collector (SEM x10,000)				
Sn deposition rate	0.5 nm/Mpls	<0.002 nm/Mpls	<0.0007 nm/Mpls	<0.0004 nm/Mpls

Works well with small droplets and a small amount of H₂ gas.

Gigaphoton's Concept

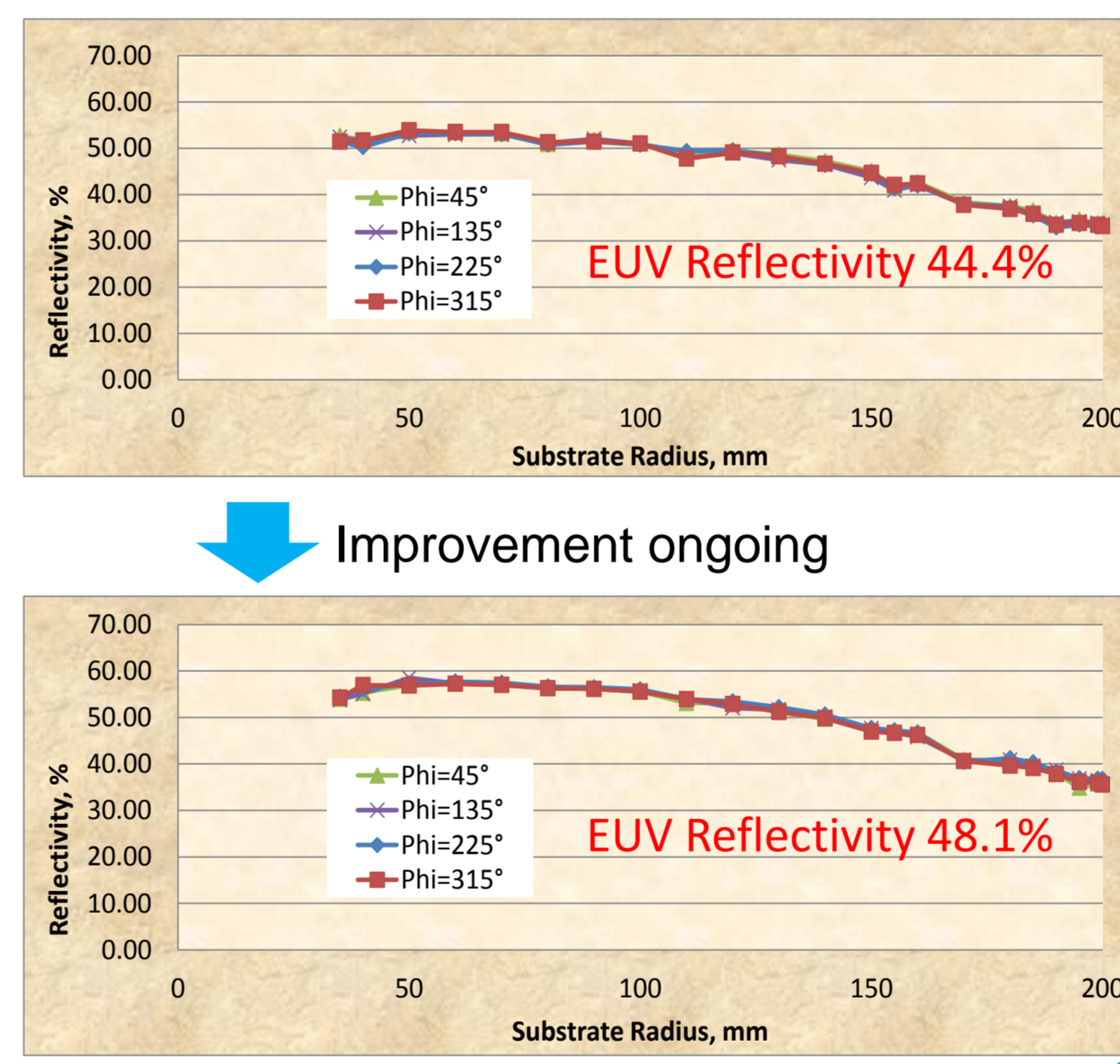
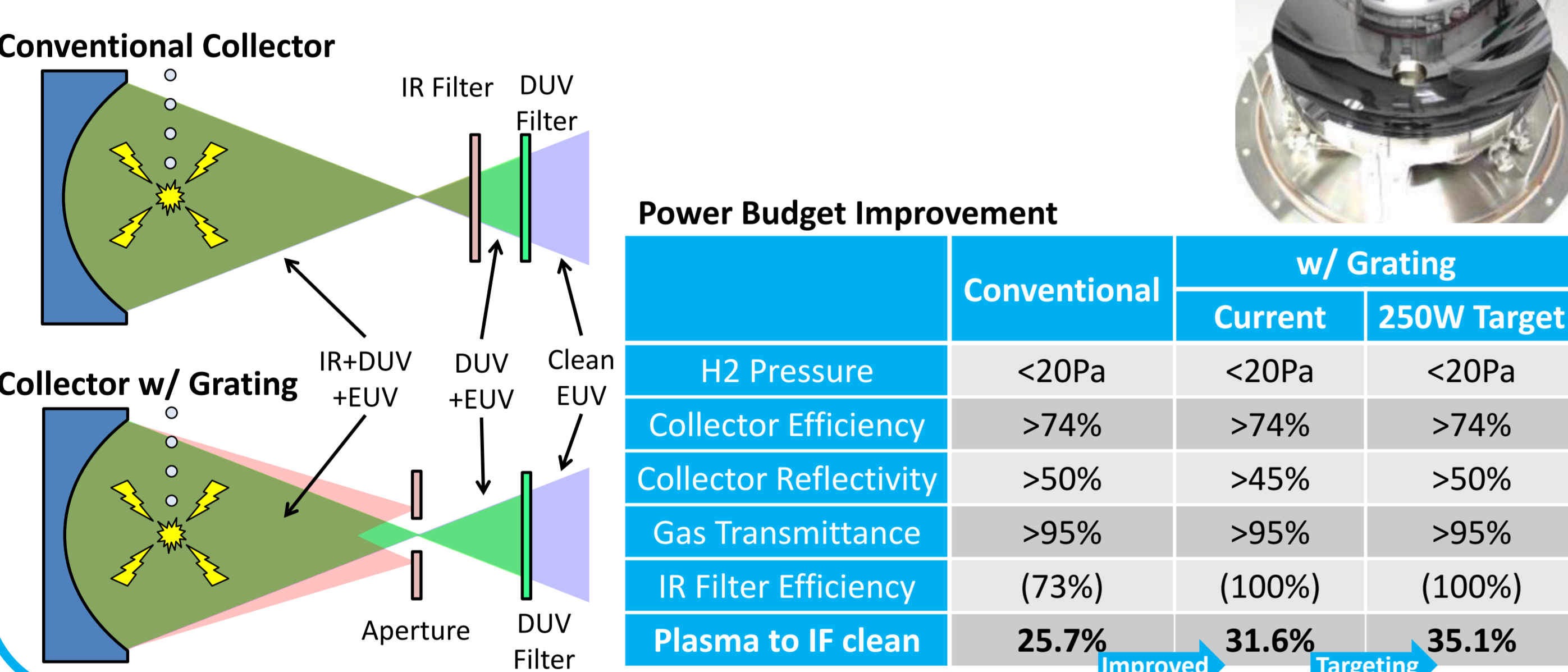


3. Pre-pulse Technology for High CE and High Ionization Rate

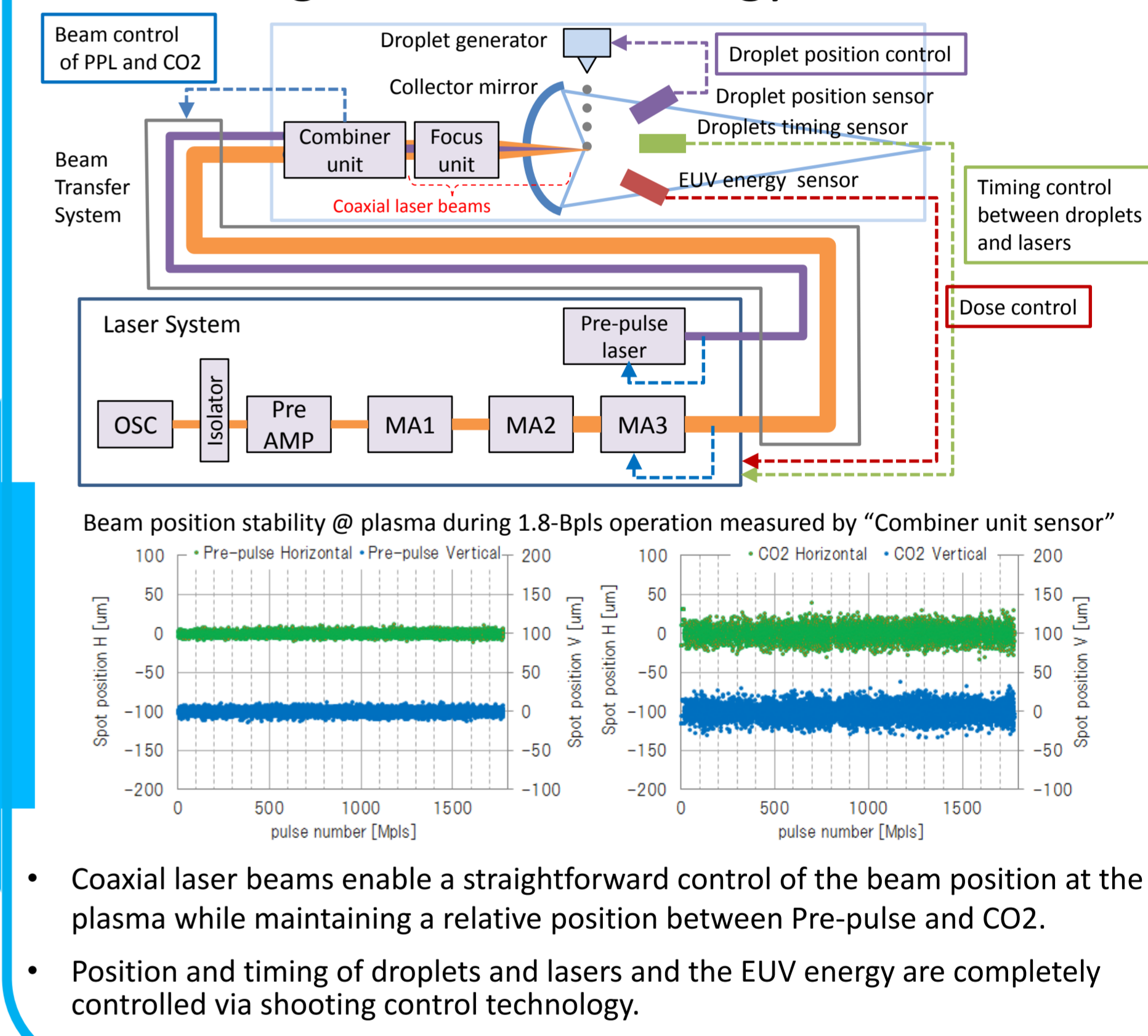


5. Collector Mirror with grating structure for highly efficient out of band light reduction

Collector with grating improves the power budget from EUV plasma to IF clean.



4. Shooting Control Technology



7. Proto system performance

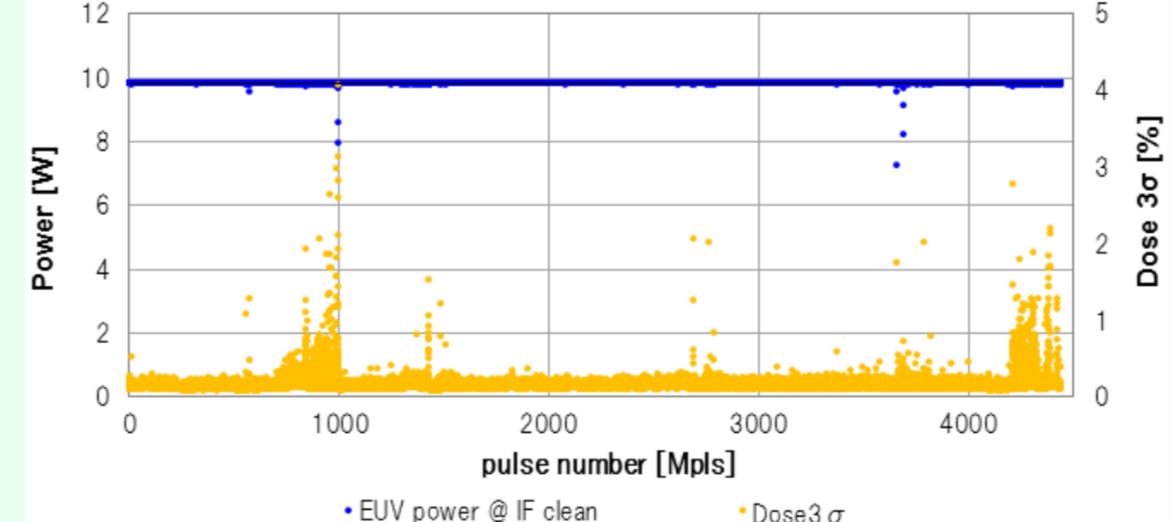
Target Specification	Proto #1	Proto #2
Purpose	Magnetic Mitigation	High power and stable operation
EUV Power	25 W	150 W
CE	3.5%	3.5%
Pulse rate	50 kHz	100 kHz
CO ₂ laser	> 3kW	> 17kW
Dose overhead	20%	
Pre-pulse	Pico second	
Debris mitigation	1 month	

Proto#1

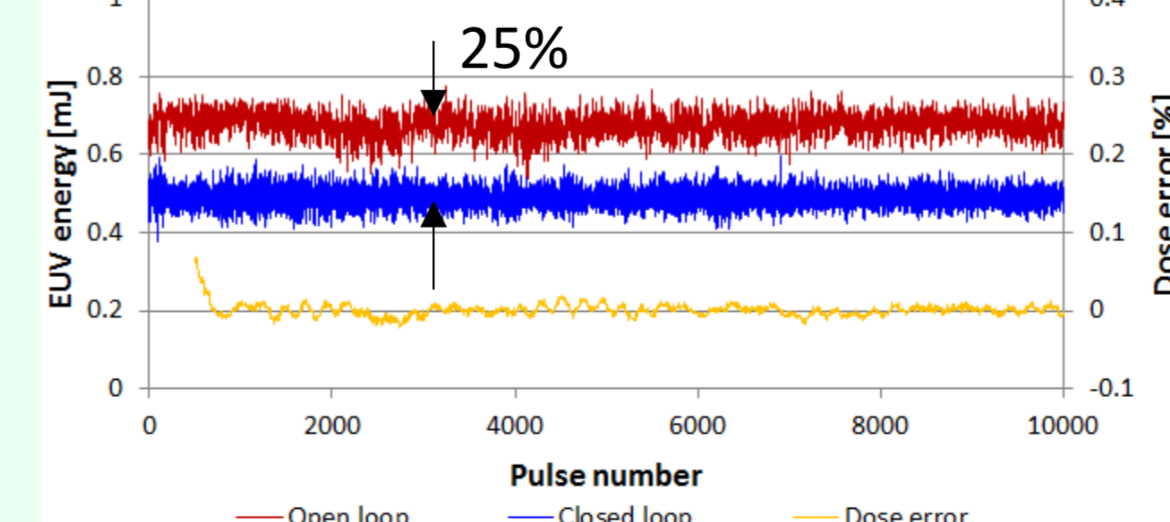
Dose controlled EUV power :10W
-pulse number: 4.5-Bpls (total)
Incl. unattended operation
-Dose error 3 σ : <0.2%
-Dose overhead : 25% constant (Target : 20%)



20kHz Operation (Closed loop)

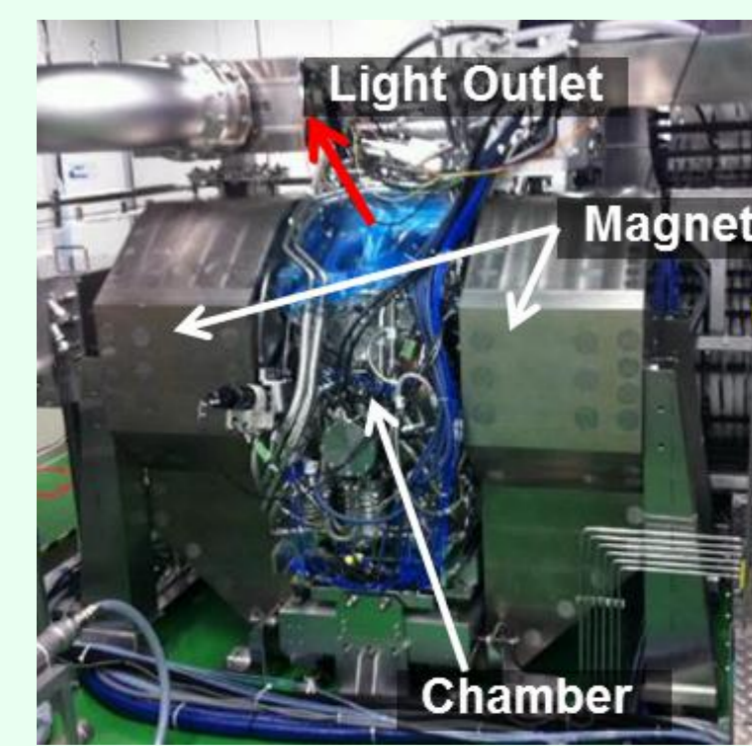


Typical pulse to pulse data

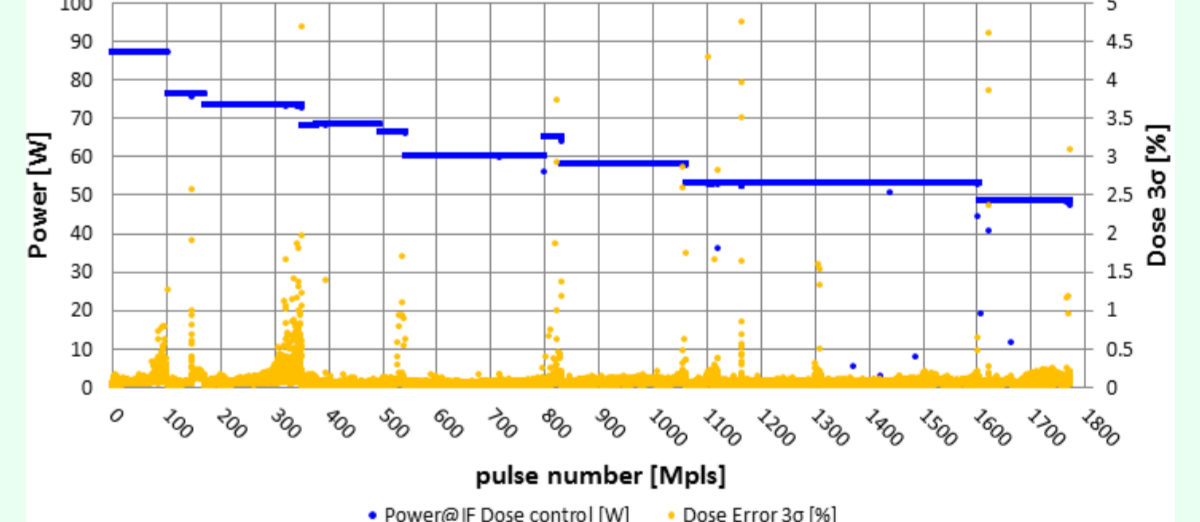


Proto#2

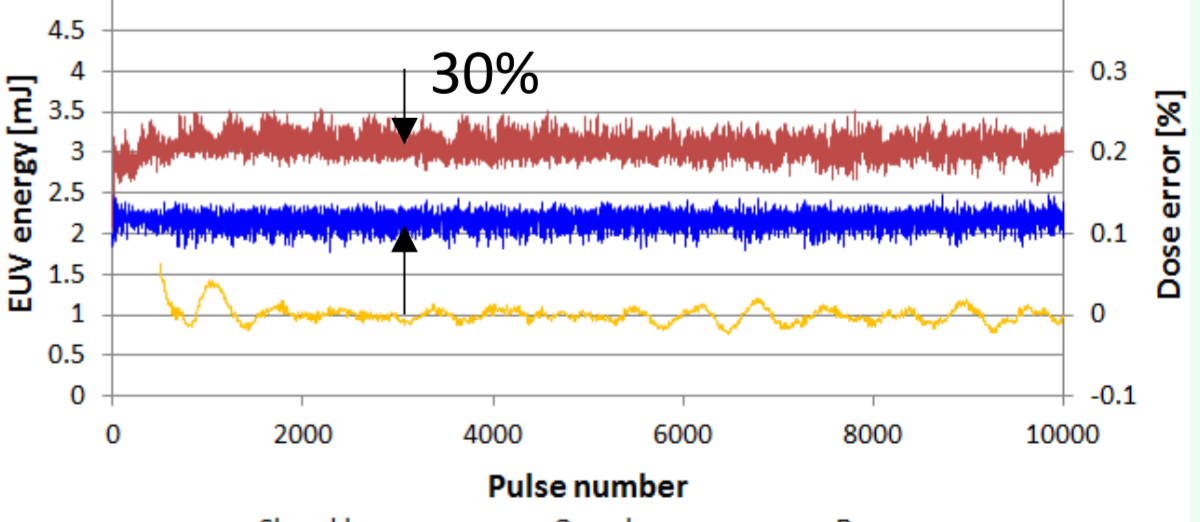
Dose controlled EUV power :49~87W
-pulse number: 1.8-Bpls (total)
Incl. unattended operation
-Dose error 3 σ : <0.2%
-Dose overhead : 30~55% (Target : 20%)



35kHz operation (Closed loop)



Typical pulse to pulse data

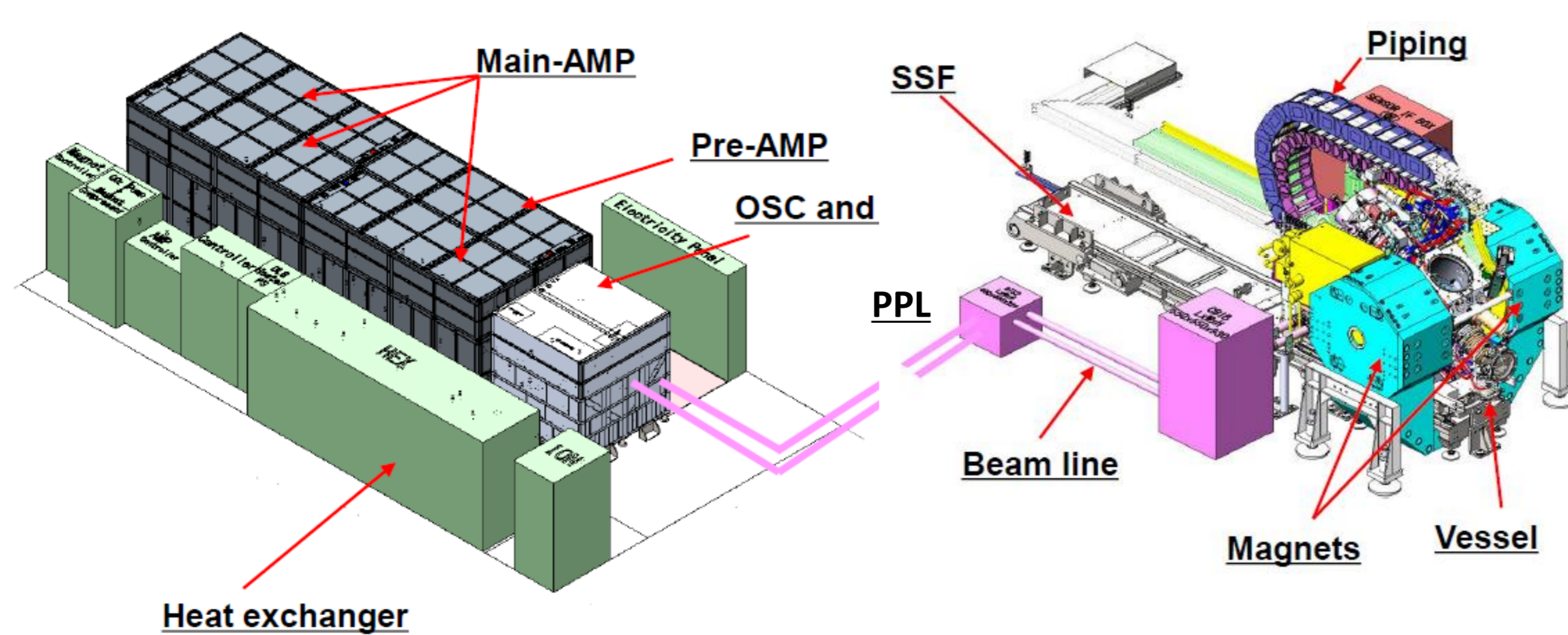


The current target is the evaluation of the intermediate focus (IF) and far field (FF).

8. Pilot system status

Pilot: Construction in progress

Target Specification	
EUV Power	250 W
CE	4.0%
Pulse rate	100 kHz
Availability	> 80%
CO ₂ laser power	>23 kW
Dose overhead	20%
Pre-pulse	Pico second
Debris Mitigation	> 1 month



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